



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
	750mΩ @ V _{GS} = -4.5V	-0.6A
-20V	1050mΩ @ V _{GS} = -2.5V	-0.5A
	1500mΩ @ V _{GS} = -1.8V	-0.45A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

- **DC-DC Converters**
- Load Switch
- **Power Management Functions**





SOT323

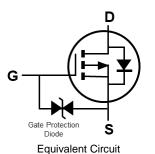
Top View

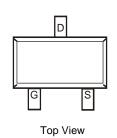
Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed Over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.006 grams (Approximate)





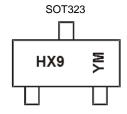
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2900UW-7	SOT323	3000/Tape & Reel
DMP2900UW-13	SOT323	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



HX9 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: G = $2\overline{0}19$) M = Month (ex: 9 = September)

Date Code Key

Year	2018	2	019	2020	2	2021	2022		2023	2024		2025
Code	F		G	Н		1	J		K	L		М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	-20	V		
Gate-Source Voltage	V_{GSS}	±6	V		
$\ (Continuous Drain (Current (Note 6)))\ _{Co} = -4.5$		$T_A = +25$ °C $T_A = +70$ °C	I _D	-0.6 -0.5	А
Maximum Body Diode Forward Current (Note 6)	Is	-0.45	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	I _{DM}	-2.5	Α		

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_{D}	0.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\Theta JA}$	393	°C/W
Total Power Dissipation (Note 6)		P_{D}	0.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\Theta JA}$	272	°C/W
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

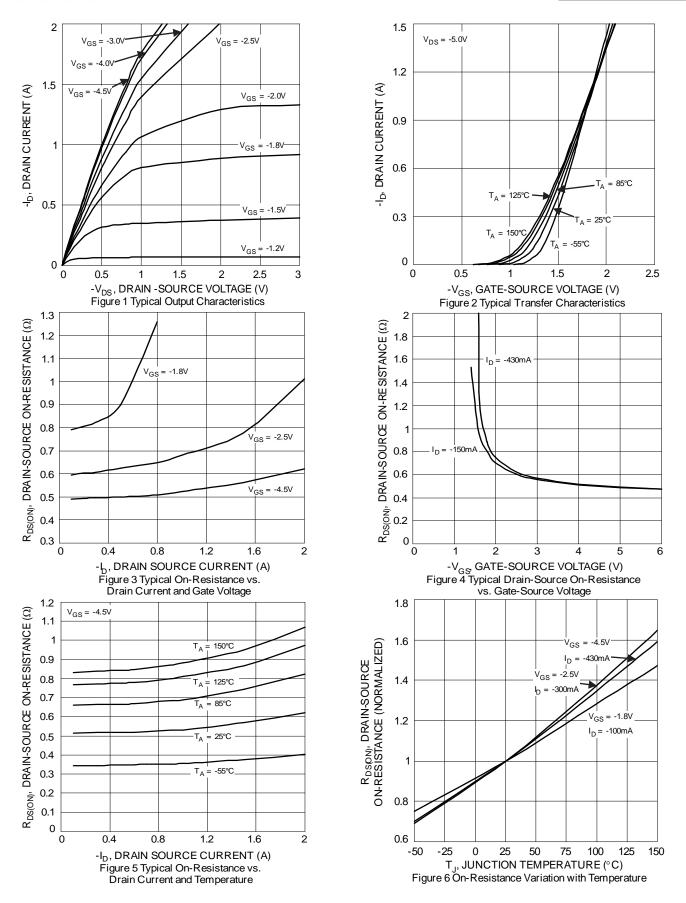
Observatoriation	0	N#!	T	M	1114	To al Comelidad	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	-100	nA	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I_{GSS}	_	_	±2.0	μΑ	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	-0.5	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			_	0.75		$V_{GS} = -4.5V$, $I_{D} = -430mA$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	_	1.05	Ω	$V_{GS} = -2.5V, I_D = -300mA$	
	, ,		_	1.5		$V_{GS} = -1.8V, I_D = -150mA$	
Diode Forward Voltage	V_{SD}	_	_	-1.2	V	V _{GS} = 0V, I _S = -150mA	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	49	_	pF	101/11/01/	
Output Capacitance	Coss	_	12	_	pF	$V_{DS} = -16V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}	_	3.4	_	pF	1 = 1.0WH2	
Total Gate Charge	Qg	_	0.7	_	nC	\\\\ 4.5\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
Gate-Source Charge	Q_{gs}	_	0.1		nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_{D} = -250$ mA	
Gate-Drain Charge	Q_{gd}	_	0.1	l	nC	ID = -230IIIA	
Turn-On Delay Time	t _{D(ON)}	_	5.3		ns	101/11/	
Turn-On Rise Time	t _R	_	2.8		ns	$V_{DD} = -10V, V_{GS} = -4.5V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	1247	_	ns	$R_L = 47\Omega$, $R_G = 10\Omega$, $R_D = -200$ mA	
Turn-Off Fall Time	t _F	_	445		ns	1D = -20011IA	
Reverse Recovery Time	t _{RR}	_	10.5	_	ns	I _F = -1.0A, di/dt = 100A/µs	
Reverse Recovery Charge	Q_{RR}	_	1.8	_	nC	IF = -1.0A, αι/αι = 100A/μS	

Notes:

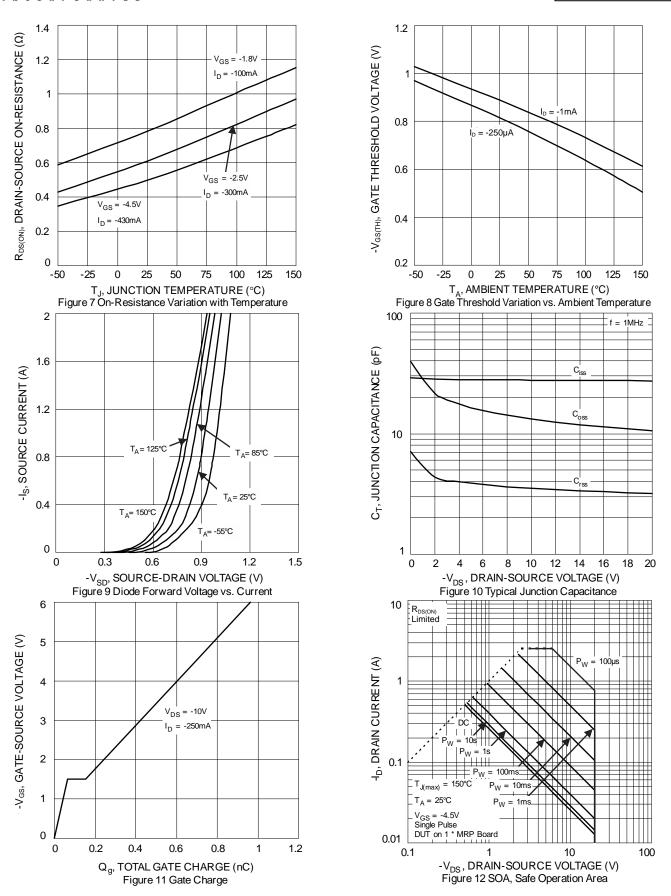
- 5. Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.6. Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.7. Short duration pulse test used to minimize self-heating effect.

- 8. Guaranteed by design. Not subject to production testing.











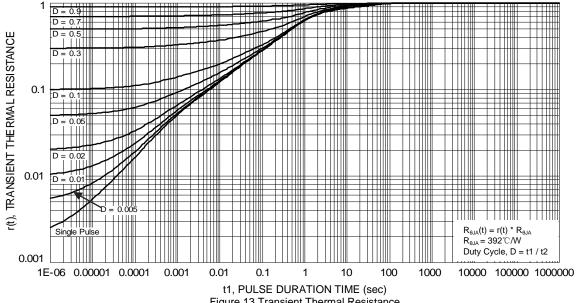


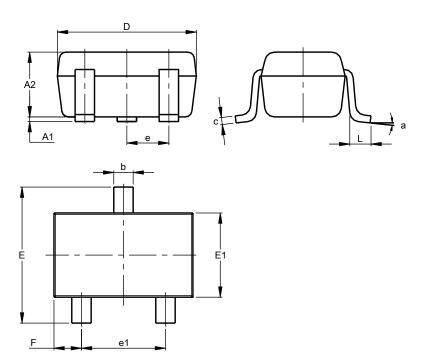
Figure 13 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323

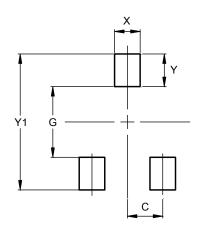


SOT323							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.25	0.40	0.30				
С	0.10	0.18	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	().650 B	SC				
e1	1.20	1.40	1.30				
F	0.375	0.475	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323



Dimensions	Value (in mm)				
С	0.650				
G	1.300				
Х	0.470				
Υ	0.600				
Y1	2.500				



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